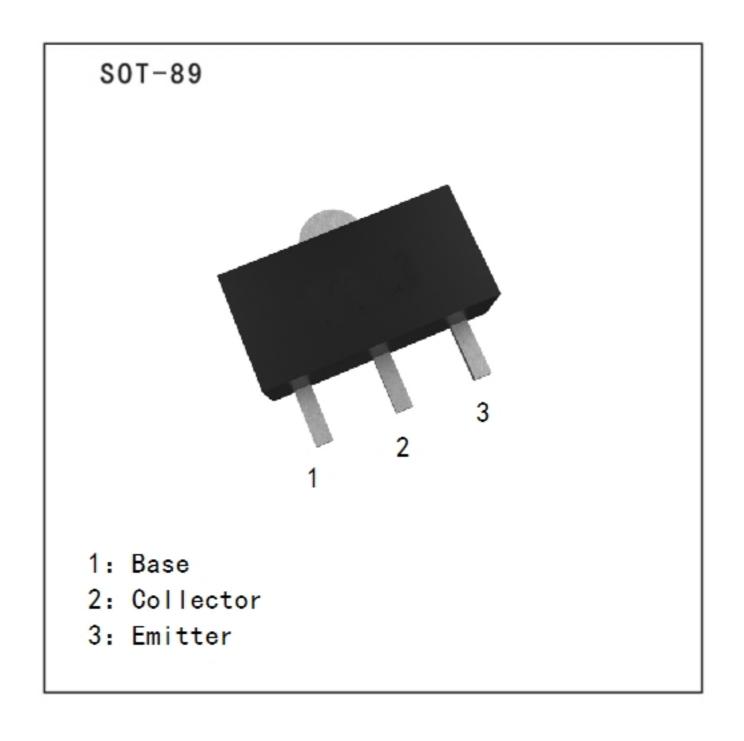


Features

High collector to emitter voltage: VCEO>-120V.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	Vсво	-120	V
Collector-emitter voltage	VCEO	-120	V
Emitter-base voltage	Vево	-5	V
Collector current	Ic	-0.7	Α
Collector current (pulse) *1	IC(pu)	-1.2	Α
Collector power dissipation	Pc	2	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

^{*1.} PW≤10ms,duty cycle≤50%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
Collector cutoff current	Ісво	Vcb = -120V, IE=0			-100	nA
Emitter cutoff current	ІЕВО	VEB = -5V, IC=0			-100	nA
DC current gain *	hFE	Vce =-1V , Ic = -100mA	90	200	400	
		Vce =-1V , Ic = -5.0mA	45	200		
Collector-emitter saturation voltage *	VCE(sat)	Ic = -500mA , Iв = -50mA		-0.4	-0.6	V
Base-emitter saturation voltage *	VBE(sat)	Ic = -500mA , IB = -50mA		-0.9	-1.5	V
Base-emitter voltage *	VBE	Vce =-10V , Ic = -10mA	-550	-620	-650	mV
Output capacitance	Cob	VCB = -10V , IE = 0 , f = 1.0MHz		14		pF
Transition frequency	fT	Vce = -10V , Ie = 10mA		75		MHz

^{*} PW≤350µs,duty cycle≤2%

hFE Classification

Marking	KR	KQ	KP
hFE	90~180	135~270	200~400

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